# 2SA1127

## Silicon PNP epitaxial planar type

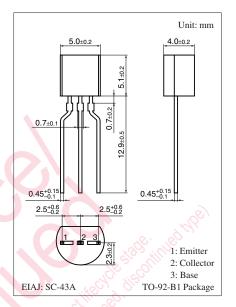
For low-frequency and low-noise amplification Complementary to 2SC2634

#### ■ Features

- Low noise voltage NV
- High forward current transfer ratio h<sub>FE</sub>

### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-60	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-55	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	-7	V	
Collector current	$I_C$	-100	mA	
Peak collector current	$I_{CP}$	-200	mA	
Collector power dissipation	P <sub>C</sub>	400	mW	
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	



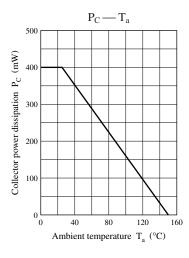
### ■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

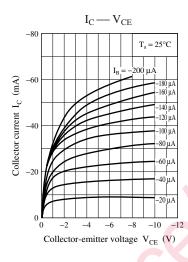
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = -10  \mu \text{A},  I_{\rm E} = 0$	-60			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = -1 \text{ mA}, I_B = 0$	-55			V
Emitter-base voltage (Collector open)	$V_{\rm EBO}$	$I_E = -10 \mu\text{A},  I_C = 0$	-7			V
Base-emitter voltage	V <sub>BE</sub>	$V_{CE} = -1 \text{ V}, I_{C} = -30 \text{ mA}$			-1	V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -10 \text{ V}, I_E = 0$		-1	-100	nA
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = -10 \text{ V}, I_{B} = 0$		- 0.01	-1.00	μΑ
Forward current transfer ratio *	$h_{FE}$	$V_{CE} = -5 \text{ V}, I_{C} = -2 \text{ mA}$	180		700	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$			- 0.6	V
Transition frequency f <sub>T</sub> V		$V_{CB} = -5 \text{ V}, I_E = 2 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Noise voltage	NV	$V_{CE} = -10 \text{ V}, I_{C} = -1 \text{ mA}, G_{V} = 80 \text{ dB}$			150	mV
		$R_g = 100 \text{ k}\Omega$ , Function = FLAT				

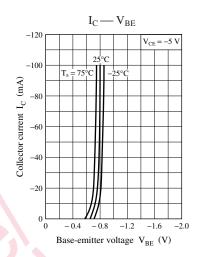
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

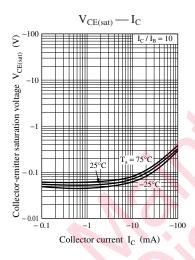
#### 2. \*: Rank classification

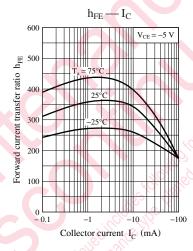
Rank	R	S	Т
$h_{FE}$	180 to 360	260 to 520	360 to 700

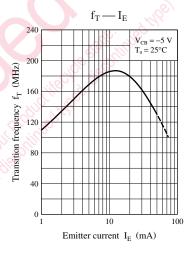


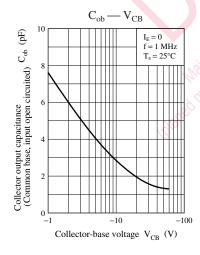


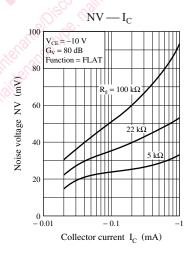












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